

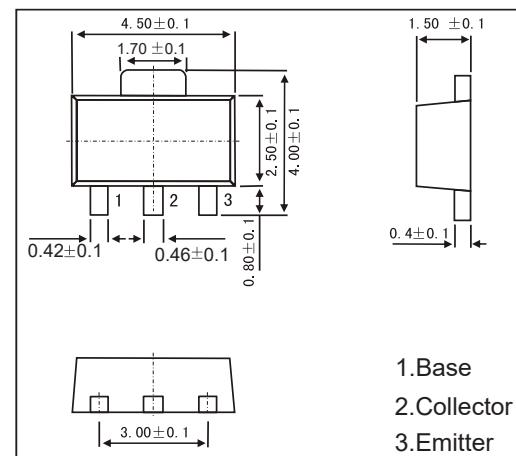
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Low collector-emitter saturation voltage
- High efficiency with low voltage power supply
- Satisfactory operation performances
- Transistors NPN

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	40	V
Collector - Emitter Voltage	V _{CEO}	25	
Emitter - Base Voltage	V _{EBO}	7	
Collector Current - Continuous	I _C	3	A
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 100 uA, I _E = 0	40			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	25			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 uA, I _C = 0	7			
Collector-base cut-off current	I _{CBO}	V _{CB} = 40 V , I _E = 0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = 7V , I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3 A, I _B =100 mA			1	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =3 A, I _B =100 mA			1.2	
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 500mA	230		600	
		V _{CE} = 2V, I _C = 2 A	150			
Collector output capacitance	C _{ob}	V _{CB} = 20V, I _E = 0,f=1MHz			50	pF
Transition frequency	f _T	V _{CE} = 6V, I _C = 50 mA,f=200MHz			150	MHz